



## N-Channel 75-V (D-S) 200°C MOSFET

### CHARACTERISTICS

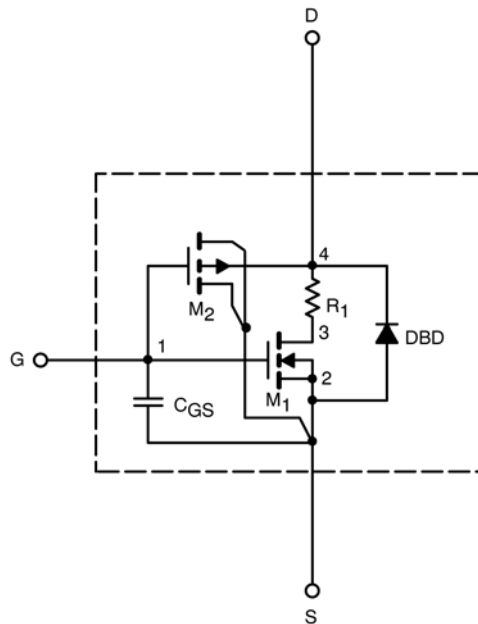
- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

### DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 to 125°C temperature ranges under the pulsed 0 to 10V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### SUBCIRCUIT MODEL SCHEMATIC



This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.



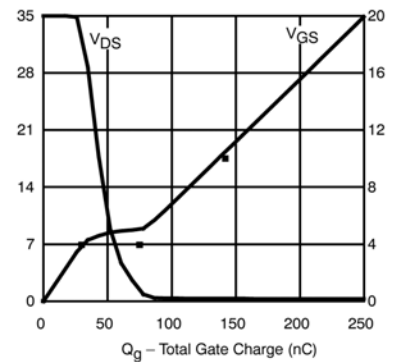
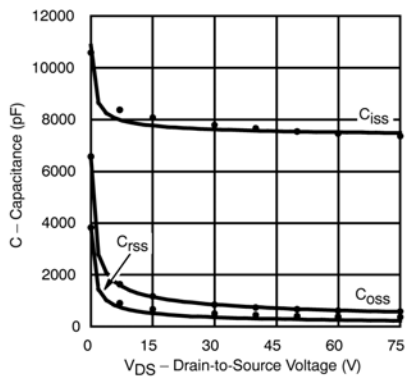
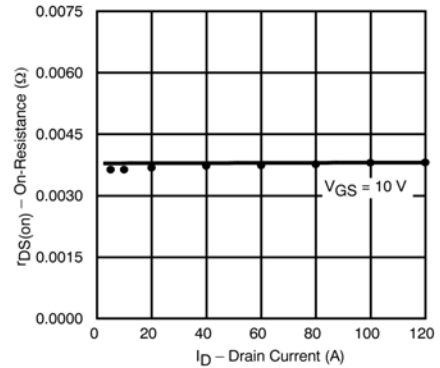
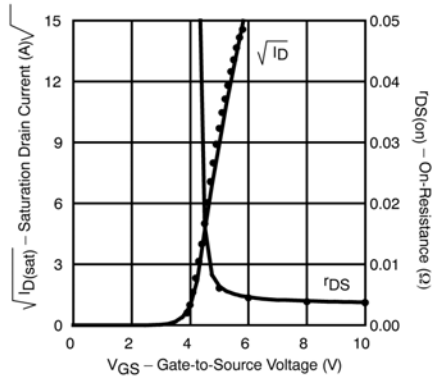
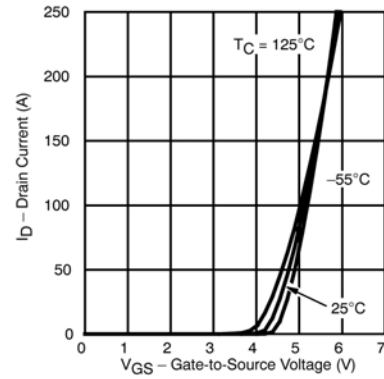
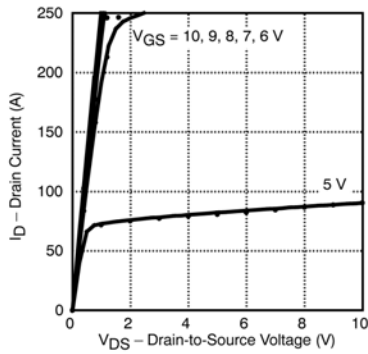
SPECIFICATIONS (T <sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	Test Conditions	Simulated Data	Measured Data	Unit
<b>Static</b>					
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3.1		V
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> > 5 V, V <sub>GS</sub> = 10 V	1197		A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A	0.0038	0.0038	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A, T <sub>J</sub> = 125°C	0.0063		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A, T <sub>J</sub> = 200°C	0.0084		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	109		S
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 110 A, V <sub>GS</sub> = 0 V	0.92	1	V
<b>Dynamic<sup>b</sup></b>					
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz	7663	7900	Pf
Output Capacitance	C <sub>oss</sub>		936	950	
Reverse Transfer Capacitance	C <sub>rss</sub>		406	550	
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 35 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 110 A	139	145	NC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>		36	30	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		45	45	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 35 V, R <sub>L</sub> = 0.40 Ω I <sub>D</sub> ≅ 110 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 2.5 Ω	88	25	Ns
Rise Time <sup>c</sup>	t <sub>r</sub>		110	200	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		130	65	
Fall Time <sup>c</sup>	t <sub>f</sub>		149	165	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 85 A, di/dt = 100 A/μs	55	80	

Notes:

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.



COMPARISON OF MODEL WITH MEASURED DATA ( $T_J=25^{\circ}\text{C}$  UNLESS OTHERWISE NOTED)



Note: Dots and squares represent measured data.